

SECURITY CLASSIFICATION OF THIS PAGE

ORT DOCUMENTATION PAGE

AD-A222 405

1b. RESTRICTIVE MARKINGS

None

3. DISTRIBUTION/AVAILABILITY OF REPORT

Unlimited

4. PERFORMING ORGANIZATION REPORT NUMBER(S)

interim technical report #35

5. MONITORING ORGANIZATION REPORT NUMBER(S)

6a. NAME OF PERFORMING ORGANIZATION

Department of Chemistry

6b. OFFICE SYMBOL (if applicable)

7a. NAME OF MONITORING ORGANIZATION

Office of Naval Research

6c. ADDRESS (City, State, and ZIP Code)

Massachusetts Institute of Technology
77 Mass. Avenue, Bldg. 6-335
Cambridge, MA 02139

7b. ADDRESS (City, State, and ZIP Code)

Chemistry Division
800 N. Quincy Street
Arlington, VA 22217

8a. NAME OF FUNDING/SPONSORING ORGANIZATION

Office of Naval Research

8b. OFFICE SYMBOL (if applicable)

9. PROCUREMENT INSTRUMENT IDENTIFICATION NUMBER

N00014-84-K-0553

8c. ADDRESS (City, State, and ZIP Code)

Chemistry division
800 N. Quincy Street
Arlington, VA 22217

10. SOURCE OF FUNDING NUMBERS

PROGRAM ELEMENT NO.	PROJECT NO.	TASK NO.	WORK UNIT ACCESSION NO.
		051-579	

11. TITLE (Include Security Classification)

Face-Specific Interaction of MoS₄²⁻ with Oriented Crystals of (0001) CdX(X = Se, S)

12. PERSONAL AUTHOR(S)

James Hickman and Mark S. Wrighton

13a. TYPE OF REPORT

technical interim

13b. TIME COVERED

FROM 5/89- TO 5/90

14. DATE OF REPORT (Year, Month, Day)

5/17/90

15. PAGE COUNT

17

16. SUPPLEMENTARY NOTATION

Prepared for publication in Journal of the American Chemical Society

COSATI CODES		
FIELD	GROUP	SUB-GROUP

18. SUBJECT TERMS (Continue on reverse if necessary and identify by block number)

cadmium sulfide, cadmium crystals, spectroscopy
pretreatment of etching procedures

19. ABSTRACT (Continue on reverse if necessary and identify by block number)

See Attached Sheet

DTIC
1990
D

20. DISTRIBUTION/AVAILABILITY OF ABSTRACT
 UNCLASSIFIED/UNLIMITED SAME AS RPT. DTIC USERS

21. ABSTRACT SECURITY CLASSIFICATION
Unlimited

22a. NAME OF RESPONSIBLE INDIVIDUAL
Mark S. Wrighton

22b. TELEPHONE (Include Area Code)
617-253-1597

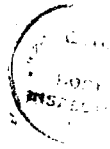
22c. OFFICE SYMBOL

Abstract

Oriented (0001) CdX (X = S, Se) crystals selectively adsorb MoS_4^{2-} onto the Cd-rich faces. Binding of MoS_4^{2-} is effected by dipping the CdX crystals into CH_3CN containing 20 mM $[\text{Et}_4\text{N}]_2\text{MoS}_4$. Removal of the crystal from the solution followed by rinsing with CH_3CN leaves MoS_4^{2-} on the Cd- but not X-rich face of the crystal as detected by X-ray photoelectron spectroscopy (XPS) and Auger electron spectroscopy (AES). The specificity for Cd-face vs. X-face binding is typically >5:1 as determined by XPS and AES data for both faces of the same crystal. S element maps for the MoS_4^{2-} -modified, Cd-face of CdSe crystals reveal non-uniform binding of MoS_4^{2-} . There is a correlation of the regions of MoS_4^{2-} binding with the crystal planes revealed in the pretreatment/etch procedure. **Keywords: cadmium sulfide,**

→ Cadmium Crystals,

→ spectroscopy, pretreatment of etching procedure. ← JG



Accession For	
NTIS GRA&I	<input checked="" type="checkbox"/>
DTIC TAB	<input type="checkbox"/>
Unannounced	<input type="checkbox"/>
Justification	
By _____	
Distribution/ _____	
Availability Codes	
Dist	Special and/or
	Special

A-1

Office of Naval Research
Contract NOOO14-84-K-0553

Task No. 051-597

Technical Report #35

Face-Specific Interaction of MoS_4^{2-} with Oriented Crystals
of (0001) CdX (X = Se, S)

by

James H. Hickman and Mark S. Wrighton

Prepared for Publication

in

Journal of the American Chemical Society

Massachusetts Institute of Technology
Department of Chemistry
Cambridge, MA 02139

Reproduction in whole or in part is permitted for any purpose of the
United States Government.

This document has been approved for public release and sale; its
distribution is unlimited.

[Prepared for publication as a Communication to the Editor
of the Journal of the American Chemical Society]

**Face-Specific Interaction of MoS_4^{2-} with Oriented Crystals
of (0001) CdX (X = Se, S)**

James J. Hickman and Mark S. Wrighton*

*Department of Chemistry
Massachusetts Institute of Technology
Cambridge, Massachusetts 02139*

*Address correspondence to this author.

Abstract

Oriented (0001) CdX (X = S, Se) crystals selectively adsorb MoS_4^{2-} onto the Cd-rich faces. Binding of MoS_4^{2-} is effected by dipping the CdX crystals into CH_3CN containing 20 mM $[\text{Et}_4\text{N}]_2\text{MoS}_4$. Removal of the crystal from the solution followed by rinsing with CH_3CN leaves MoS_4^{2-} on the Cd- but not X-rich face of the crystal as detected by X-ray photoelectron spectroscopy (XPS) and Auger electron spectroscopy (AES). The specificity for Cd-face vs. X-face binding is typically >5:1 as determined by XPS and AES data for both faces of the same crystal. S element maps for the MoS_4^{2-} -modified, Cd-face of CdSe crystals reveal non-uniform binding of MoS_4^{2-} . There is a correlation of the regions of MoS_4^{2-} binding with the crystal planes revealed in the pretreatment/etch procedure.

We wish to communicate that MoS_4^{2-} adsorbs selectively on the Cd-rich face of oriented crystals of (0001) CdX (X = S, Se) and that the binding to the Cd-rich face is non-uniform. We have used X-ray photoelectron spectroscopy (XPS) and Auger electron spectroscopy (AES) to demonstrate the selectivity of the MoS_4^{2-} adsorption on CdX. In this work we have extended previous studies on the interaction of anionic S-donor species such as dithiocarbamates,¹ thiolates,²⁻⁴ and polysulfides⁵⁻⁷ on CdX crystals. Such studies reveal that anionic S-donors can strongly and favorably influence the CdX/electrolyte interface energetics to give highly efficient photoelectrochemical devices.^{1-3,5-7.} Differential capacitance measurements have shown that the Cd-, but not S-, face of (0001) CdS interacts strongly with S^{2-} .⁸ More recently it has been shown that $\text{Fe}(\text{CN})_6^{3-/4-}$ interacts favorably only with the Cd-rich face of CdX.⁹ This study was undertaken to better understand the role of crystal orientation in determining the degree of interaction of CdX with anionic S-donor compounds. We chose to investigate MoS_4^{2-} as an adsorbate, because of its high charge to size ratio.

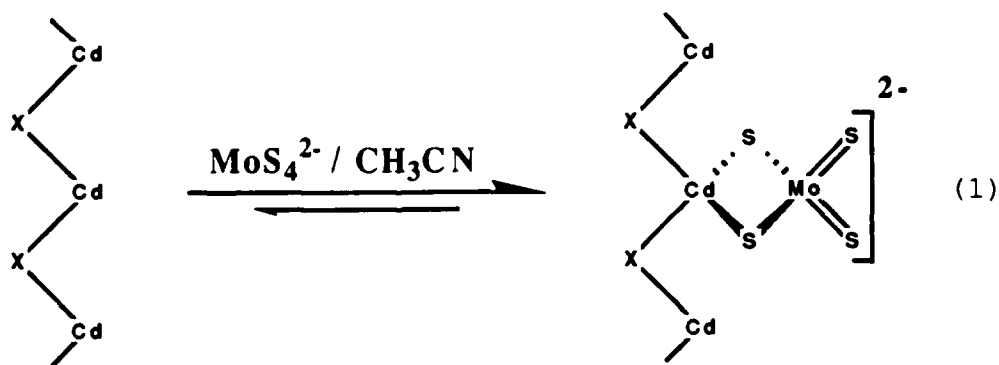
Experiments were carried out using n-type CdX single crystals (1-2 mm thick and 0.2-0.4 cm² in area from Cleveland Crystals, Cleveland, Ohio) cut perpendicular to the c-axis to expose the (0001) face. The CdX crystals were first cleaned in concentrated H_2SO_4 to remove C-containing

deposits. The CdS crystals were then etched in 12 M HCl¹⁰ for 30 s and rinsed with copious amounts of H₂O and then with CH₃CN. The CdSe crystals were etched in a 3:1 mixture of HCl:HNO₃ for 15 s, rinsed with H₂O, and then exposed to a 1 M KCN solution for 5-10 min.¹⁰ The crystals were finally rinsed with H₂O and then with CH₃CN. AES analysis of the etched CdX crystals indicates the presence of some adventitious C and O, but no other contaminating elements were detected.

The CdX crystals were modified with MoS₄²⁻ by immersing them for 5 min in a 20 mM solution of [Et₄N]₂MoS₄¹¹ dissolved in distilled and deoxygenated CH₃CN. The crystals were then rinsed with CH₃CN for 1-2 min and stored under vacuum prior to introduction into the spectrometer. The crystals were examined by XPS and/or AES.¹²

CdS crystals modified with MoS₄²⁻ were examined principally by XPS because the element Mo is much more easily detected by XPS than AES. CdSe crystals were examined by AES (for S) and XPS (for Mo and S). Both AES and XPS show selective binding of MoS₄²⁻ to the Cd-rich face of CdX. Representative XPS data are shown in Figure 1 for CdS. Spectra were taken on both sides of the same crystal to eliminate artifacts arising from differences between crystals, and essentially the same result was found for each of >10 independently prepared samples. The Mo signal on the Cd-rich face is at least five times that on the X-rich face. The peak energy of the Mo 3d_{5/2} signal is 232.6 eV (using

$\text{Cd}^{2+} 4d_{5/2}$ at 405.1 eV as a reference) which is consistent with Mo(VI)^{13} and suggests that the MoS_4^{2-} remains intact after adsorption onto the surface of the crystal. The Mo/S ratio and peak positions in the XPS of MoS_4^{2-} -treated CdSe are the same as for pure $[\text{Et}_4\text{N}]_2\text{MoS}_4$. The S 2s peak (on CdS) and Se 3s peak (on CdSe) in XPS measurements were used to calibrate the absolute magnitude of the Mo 3d peaks, and we conclude that there is roughly one monolayer of MoS_4^{2-} on the Cd-rich face of CdX. Prolonged washing of the MoS_4^{2-} -treated CdX with CH_3CN does lead to removal of the Mo signal. The results are consistent with reversible binding of intact MoS_4^{2-} to the Cd-rich face of (0001) CdX represented in equation (1).



The SEM of the Cd-rich face of CdSe, Figure 2, shows a surface with many sharp ridges, irregularities, and etch pits. The etch pits consist of planes of differing crystallographic orientation. Comparison of the S map from AES to the SEM indicates that the MoS_4^{2-} interacts only with certain features on the Cd-rich face of CdSe. This pattern of S AES signals does not arise from differential charging,

because the Cd map from AES is uniform over the region where there is significant variation of the S. The results for (0001) CdSe show that MoS_4^{2-} adsorbs selectively on the Cd-rich face, but the binding on the Cd-face is non-uniform.

Studies are in progress to pursue the relation between the extent of surface non-uniformity (and crystal orientation) and the magnitude of the flat-band potential shift of CdX in solvent/electrolyte media as a function of adsorbate (MoS_4^{2-}) concentration. Frequency dependent interfacial capacitance measurements¹⁴ have been interpreted to mean that the Cd face of (0001) CdS is composed of regions with different flat-band potentials. Differences in surface morphology of the Cd-rich face and the S-rich face are revealed by SEM and may be a factor in the face selective binding of MoS_4^{2-} . For now, however, it is tempting to conclude that selective binding of MoS_4^{2-} occurs at sites that can best accommodate the structure represented in equation (1).

Aside from CdX/adsorbate interactions, several III-V semiconductor/adsorbate systems are of interest. These include GaAs functionalized with Ru,¹⁵ Co,¹⁶ and Os¹⁷ and the selective modification of (111) InP on the P-rich face.¹⁸ These systems are to be investigated by scanning AES to establish whether modification is uniform.

Acknowledgement. We thank the United States Department of Energy, Office of Basic Energy Sciences, Division of

Chemical Sciences for support of this research. We acknowledge use of XPS and Auger facilities acquired through the joint Harvard/M.I.T. University Research Initiative funded by the Defense Advanced Research Projects Agency.

References

1. Thackeray, J.W.; Natan, M.J.; Ng, P.; Wrighton, M.S. *J. Am. Chem. Soc.* **1986**, *108*, 357.
2. Natan, M.J.; Thackeray, J.W.; Wrighton, M.S. *J. Phys. Chem.* **1986**, *90*, 4089.
3. (a) Josseaux, P.; Kirch-De Mesmaeker, A.; Riga, J.; Verbist, J. *J. Electrochem. Soc.* **1983**, *130*, 1067; (b) Aruchamy, A.; Venkatarathnam, A.; Subrahamnyam, M.; Subba Rao, G.V.; Aravamudan, G. *Electrochem. Acta* **1982**, 701.
4. (a) Josseaux, P.; Kirsch-De Mesmaeker, A.; Roche, A.; Romand, M.; Montes, H. *J. Electrochem. Soc.* **1985**, *132*, 684; (b) Dewitt, R.; Kirsch-De Mesmaeker, A. *Appl. Phys. Lett.* **1984**, *45*, 145; (c) Dewitt, R.; Kirsch-De Mesmaeker, A. *J. Electrochem. Soc.* **1983**, *130*, 1995; (d) Kirsch-De Mesmaeker, A.; Josseaux, P.; Nasielski, J.; Defosse, C. *Solar Energy Mat.* **1982**, *6*, 429; (e) Kirsch-De Mesmaeker, A.; Decoster, A.M.; Nasielski, J. *Solar Energy Mat.* **1981**, *4*, 203.
5. Ellis, A.B.; Kaiser, S.W.; Bolts, J.M.; Wrighton, M.S. *J. Am. Chem. Soc.* **1977**, *99*, 2839.
6. Heller, A.; Chang, K.C.; Miller, B. *J. Electrochem. Soc.* **1977**, *124*, 697.

7. Minoura, H.; Oki, T.; Tsuiki, M. *Chem. Lett.* **1976**, 1279.

8. Minoura, H.; Wantanabe, T.; Oki, T.; Tsuiki, M. *Jpn. J. Appl. Phys.* **1977**, 16, 865.

9. Rubin, H.D.; Arent, D.J.; Humphrey, B.D.; Bocarsly, A.B. *J. Electrochem. Soc.* **1987**, 134, 93.

10. Gatos, H.C.; Lavine, M.C. In *Progress in Semiconductors*; Gibson, A.F., Burgess, R.E., Eds.; CRC Press: Cleveland, OH, 1965, Vol. 8, pp 36-42.

11. Friesen, G.D.; McDonald, J.W.; Newton, W.E.; Euler, W.B.; Hoffman, B.M. *Inorg. Chem.* **1983**, 22, 2202.

12. (a) Auger electron spectra were recorded on a PHI 660 Scanning Auger Microprobe employing a 15 KeV, 10-20 nA electron beam for excitation. SEM micrographs were recorded on the same instrument at 15 KeV and 1-2 nA electron beam excitation energy. Samples were attached and grounded to the stage with metal screws. (b) X-ray photoelectron spectroscopy was taken on an SSL 100 spectrometer. Samples were attached to the stage via metal clips. The Cd 3d_{5/2} peak (405.1 eV binding energy) was monitored as the reference and was used to correct for sample charging. The X-ray line used for excitation was the Al K α line at 1486.6

eV. AES and XPS reference data for Cd, S, Se, and Mo can be found in: Handbook of Auger Electron Spectroscopy, 1978 (AES) and Handbook of X-ray Photoelectron Spectroscopy, 1979 (XPS) published by Perkin-Elmer Corp., Eden Prairie, MN.

13. Nefedou, V.I.; Salyn, Ya. V.; Leonhardt, G.; Scheibe, R. *J. Elect. Spectros.* **1977**, *10*, 121.

14. Braun, C.M.; Fujishima, A.; Honda, K. *Chem. Lett.* **1985**, 1763.

15. Parkinson, B.A.; Heller, A.; Miller, B. *Appl. Phys. Lett.* **1978**, *33*, 521.

16. Abrahams, I.L.; Tufts, B.J.; Lewis, N.S. *J. Am. Chem. Soc.* **1987**, *109*, 3472.

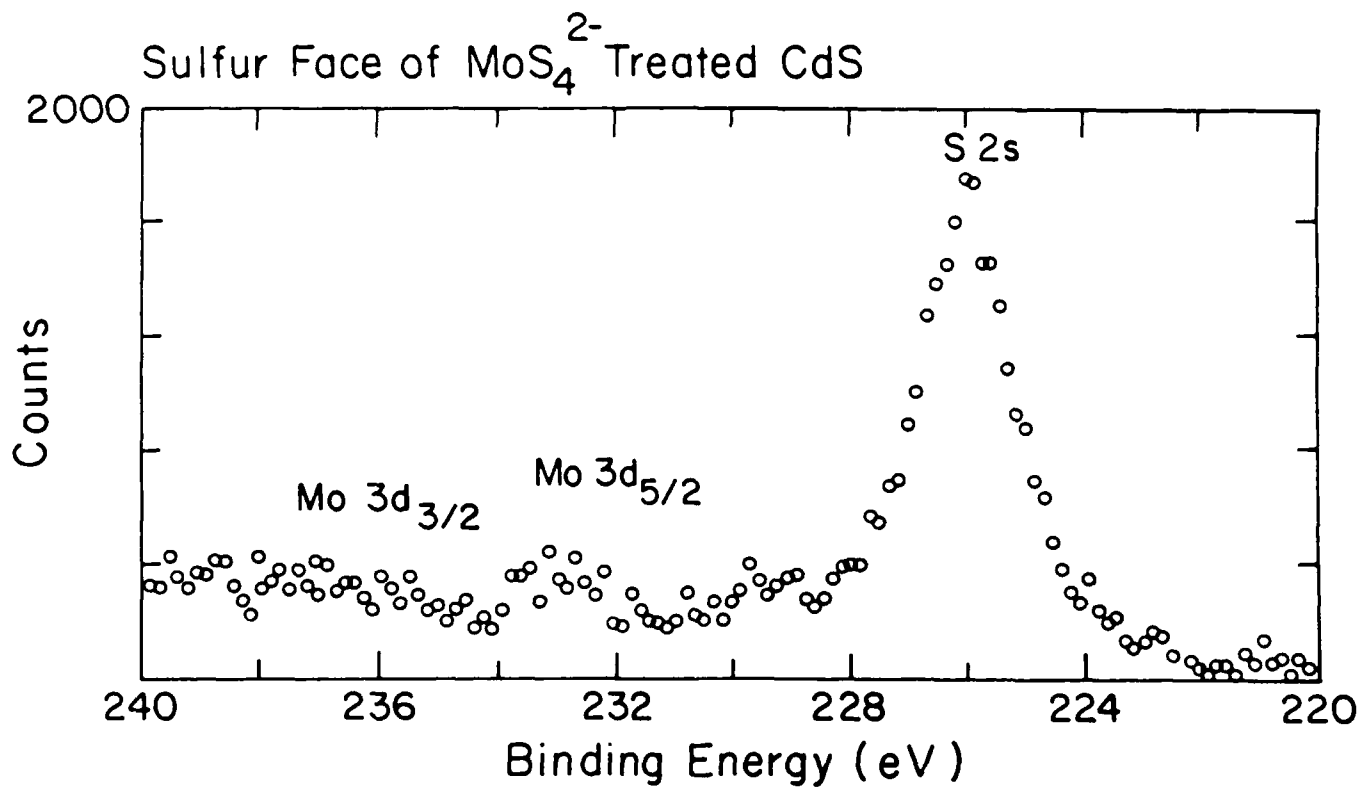
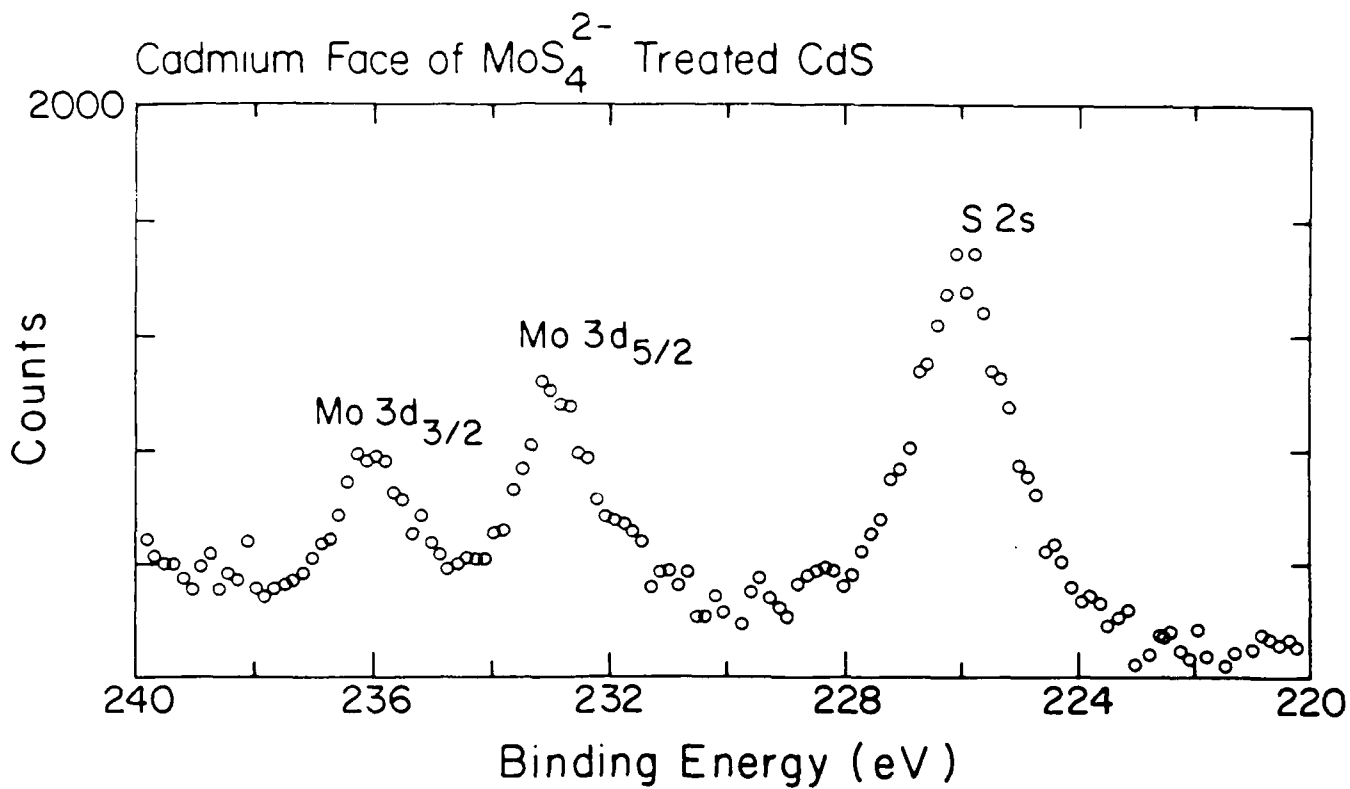
17. Tufts, B.J.; Abrahams, I.L.; Santangelo, P.G.; Ryba, G.N.; Casagrande, L.G.; Lewis, N.S. *Nature* **1987**, *326*, 861.

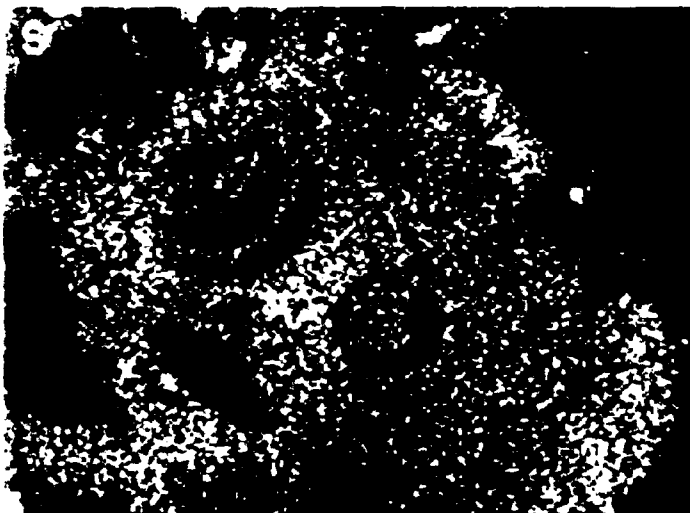
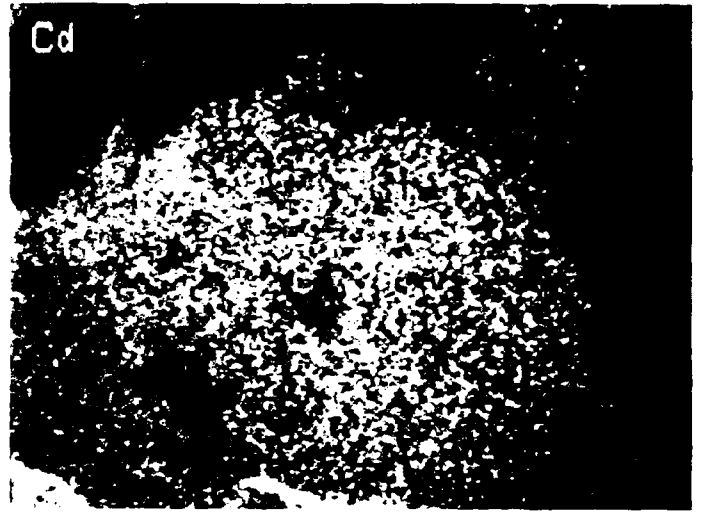
18. Spool, A.M.; Daube, K.A.; Mallouk, T.E.; Belmont, J.A.; Wrighton, M.S. *J. Am. Chem. Soc.* **1986**, *108*, 3155.

Figure Captions

Figure 1. XPS data showing MoS_4^{2-} adsorption on only the Cd-rich face of oriented (0001) CdS.

Figure 2. Three element maps (S, C, and Cd) of an etch-pit on the Cd-rich face of (0001) CdSe depicted in the SEM in upper left corner. The surface concentration of the elements is proportional to the brightness in each photograph. Carbon is adventitious from exposure to atmosphere after MoS_4^{2-} interaction. Note the Cd signal is obscured where the C coverage appears large.





TECHNICAL REPORT DISTRIBUTION LIST - GENERAL

Office of Naval Research (2)
Chemistry Division, Code 1113
800 North Quincy Street
Arlington, Virginia 22217-5000

Commanding Officer (1)
Naval Weapons Support Center
Dr. Bernard E. Douda
Crane, Indiana 47522-5050

Dr. Richard W. Drisko (1)
Naval Civil Engineering
Laboratory
Code L52
Port Hueneme, CA 93043

David Taylor Research Center (1)
Dr. Eugene C. Fischer
Annapolis, MD 21402-5067

Dr. James S. Murday (1)
Chemistry Division, Code 6100
Naval Research Laboratory
Washington, D.C. 20375-5000

Dr. Robert Green, Director (1)
Chemistry Division, Code 385
Naval Weapons Center
China Lake, CA 93555-6001

Chief of Naval Research (1)
Special Assistant for Marine
Corps Matters
Code 00MC
800 North Quincy Street
Arlington, VA 22217-5000

Dr. Bernadette Eichinger (1)
Naval Ship Systems Engineering
Station
Code 053
Philadelphia Naval Base
Philadelphia, PA 19112

Dr. Sachio Yamamoto (1)
Naval Ocean Systems Center
Code 52
San Diego, CA 92152-5000

Dr. Harold H. Singerman (1)
David Taylor Research Center
Code 283
Annapolis, MD 21402-5067

ENCLOSURE(2)